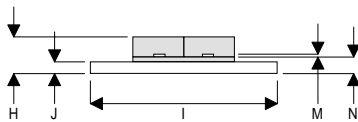
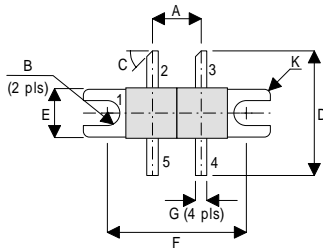


MECHANICAL DATA

**GOLD METALLISED
MULTI-PURPOSE SILICON
DMOS RF FET
20W – 12.5V – 1GHz
PUSH-PULL**



DK

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1
 PIN 3 DRAIN 2 PIN 4 GATE 2
 PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
A	6.45	0.13	0.254	0.005
B	1.65R	0.13	0.065R	0.005
C	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
H	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.13	0.02	0.005	0.001
N	2.16	0.13	0.085	0.005

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from 1MHz to 2 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	83W
BV_{DSS}	Drain – Source Breakdown Voltage *	40V
BV_{GSS}	Gate – Source Breakdown Voltage *	$\pm 20V$
$I_{D(sat)}$	Drain Current *	8A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

* Per Side

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PER SIDE					
BV_{DSS} Drain-Source Breakdown Voltage	$V_{GS} = 0$ $I_D = 10\text{mA}$	40			V
I_{DSS} Zero Gate Voltage Drain Current	$V_{DS} = 12.5\text{V}$ $V_{GS} = 0$			4	mA
I_{GSS} Gate Leakage Current	$V_{GS} = 20\text{V}$ $V_{DS} = 0$			4	μA
$V_{GS(th)}$ Gate Threshold Voltage *	$I_D = 10\text{mA}$ $V_{DS} = V_{GS}$	0.5		7	V
g_{fs} Forward Transconductance *	$V_{DS} = 10\text{V}$ $I_D = 0.8\text{A}$	0.72			S
TOTAL DEVICE					
G_{PS} Common Source Power Gain	$P_O = 20\text{W}$	10			dB
η Drain Efficiency	$V_{DS} = 12.5\text{V}$ $I_{DQ} = 0.8\text{A}$	40			%
VSWR Load Mismatch Tolerance	$f = 1\text{GHz}$	20:1			—
PER SIDE					
C_{iss} Input Capacitance	$V_{DS} = 0$ $V_{GS} = -5\text{V}$ $f = 1\text{MHz}$			48	pF
C_{oss} Output Capacitance	$V_{DS} = 12.5\text{V}$ $V_{GS} = 0$ $f = 1\text{MHz}$			40	pF
C_{rss} Reverse Transfer Capacitance	$V_{DS} = 12.5\text{V}$ $V_{GS} = 0$ $f = 1\text{MHz}$			4	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

$R_{THj-case}$	Thermal Resistance Junction – Case	Max. 2.1 $^{\circ}\text{C} / \text{W}$
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